AW313A Datasheet

Zhuhai Jieli Technology Co.,LTD

Version 1.1

Date 2024.07.08

Copyright © Zhuhai Jieli Technology Co.,LTD. All rights reserved.



Revision History

Date	Revision	Description
2024.04.12	V1.0	Initial Release
		Update Pin Assignment
2024.07.08	V1.1	Update Package Information
		Update IC Marking Information





Table of Contents

Re	vision History	1
Та	ble of Contents	 2
A۷	V313A Features	 3
1	Block Diagram	4
2	Pin Definition	5
	2.1 Pin Assignment	5
	2.2 Pin Description	6
3		
	3.1 Absolute Maximum Ratings	8
	3.2 ESD Ratings	8
	3.3 PMU Characteristics	 8
	3.5 BT Characteristics	10
4	Package Information	11
	4.1 QFN20L_3×3mm	11
5	IC Marking Information	12
6	Solder-Reflow Condition	13



AW313A Features

SYSTEM

- 32bit CPU 160MHz
- Support MATH/AES128
- I-cache
- Support EMU
- On-chip SRAM 32kbyte
- Support MPU
- Support UDMA
- Built-In Flash
- 24MHz crystal oscillator
- > Internal low jitter low power RC oscillator
- Internal PLL

Bluetooth

- BLE5.4 +2.4GHz-Proprietary (QDID 223418)
- Support AoA Transmitter
- Support long range BLE
- Maximum transmitting power 9dBm
- Receiver sensitivity
 - ❖ -96dBm @BLE-1Mbps
 - ◆ -93dBm @BLE-2Mbps

Peripherals

- 1 x Full speed USB
- 4 x Multi-function 32bit timer
- ➤ 1 x IR RX/TX
- 3 x UART interface
- 1 x I²C Master/Slave interface
- 2 x SPI Master/Slave interface
- ➤ 1 x QDEC
- ➤ 4 x MCPWM
- ➤ 2 x LEDC
- 1 x 10bit ADC(13 Channel)
- 12 x GPIO Support function remapping

PMU

- Support temperature sensor
- ➤ VPWR range 2.7V to 5.5V
- ➤ IOVDD range 1.8V to 3.6V
- > Deep sleep mode (IOVDD @3.0V)
 - 170nA (External wakeup)
 - 1.37uA (32kHz RC OSC+wakeup)
 - 2.9uA (32kHz RC OSC+wakeup+16k retention SRAM)

Packages

QFN20L(3mm*3mm)

Temperature

- Operating temperature
 - TC = -20° C to $+85^{\circ}$ C (standard range)
 - TC = -40° C to $+105^{\circ}$ C (extended range)
- Storage temperature -65°C to +150°C

Applications

- Mouse devices
- Non-audio remote controller
- Selfie stick
- Page turner
- Adaptive USB
- Bluetooth moudle
- Price tag and other diversified IOT product



1 Block Diagram

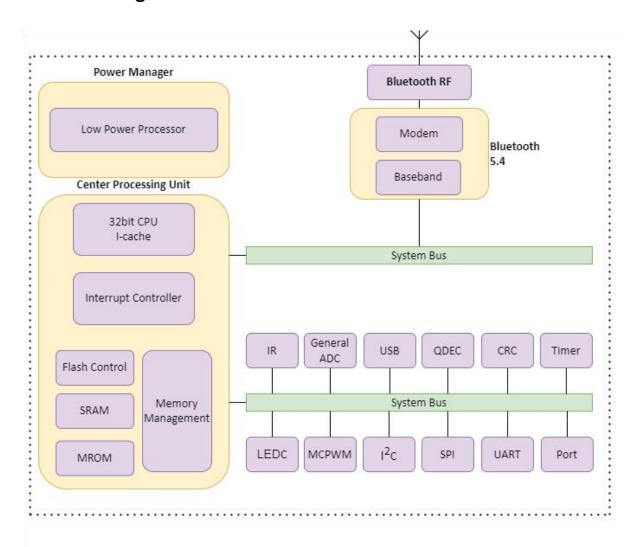


Figure 1-1 AW313A Block Diagram



2 Pin Definition

2.1 Pin Assignment

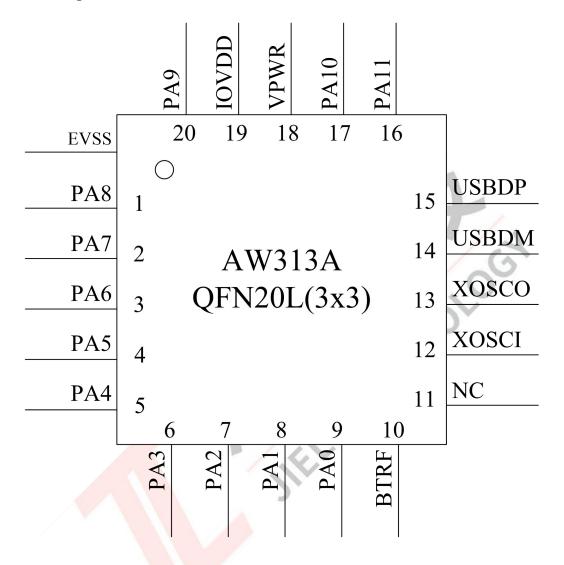


Figure 2-1 AW313A Pin Assignment



2.2 Pin Description

Table 2-2-1 AW313A Pin Description

Pin No.	Name	Туре	IO Initial State	Description
_			_	ADC8(ADC Input Channel 8)
1	PA8	1/0	Z	SPIO_DAT2B
2	PA7	1/0	Z	
3	PA6	1/0	Z	ADC6(ADC Input Channel 6)
4	PA5	1/0	Z	ADC5(ADC Input Channel 5)
F	DA4	1/0	10k0 Dull	ADC4(ADC Input Channel 4)
5	PA4	1/0	10kΩ Pull-up	MCLR(Device Reset)
6	PA3	1/0	Z	ADC3(ADC Input Channel 3)
0	PAS	170		SPIO_DIB(1)
7	PA2	1/0	Z	ADC2(ADC Input Channel 2)
,	FAZ	170		SPIO_DOB(0)
8	PA1	I/O	Z	ADC1(ADC Input Channel 1)
	171	1,0		SPIO_CLKB
9	PA0	1/0	Z	ADC0(ADC Input Channel 0)
10	BTRF	RF		Bluetooth RF Antenna
11	NC		- /	No Connection
12	XOSCI	I	-/	Crystal Oscillator Input
13	xosco	0		Crystal Oscillator Output
14	USBDM	1/0	15kΩ Pull-down	ADC13(ADC Input Channel 13)
15	USBDP	1/0	15kΩ Pull-down	ADC14(ADC Input Channel 14)
16	PA11	1/0	10kΩ Pull-up	ADC11(ADC Input Channel 11)
10	PAII	1/0	10Kt2 Pull-up	Hold down 0 to reset
17	PA10	1/0	Z	ADC10(ADC Input Channel 10)
18	VPWR	Р		Battery Input
19	IOVDD	Р		IO Power
			7	LVD(External Low Voltage Detection Input)
20	PA9	1/0	Z	ADC9(ADC Input Channel 9)
				SPIO_DAT3B

Note

1.IO initial state abbreviations Z--High resistance, H--High level, L--Low level, X--May be changed during power on.

2.Timer, IR,MCPWM, QDEC, UART, LEDC, I²C, SPI1 functions can be remapped to any I/O.

Table 2-2-2 Pin Types Description

Pin Type	Description	Pin Type	Description
Р	Power	I/O	Input or Output
G	Ground	I	Input

Copyright © 2024 Zhuhai Jieli Technology Co., LTD



Pin Type	Description	Pin Type	Description
RF	RF antenna	0	Output





3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1 Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-20	+85	$^{\circ}$
Tstg	Storage temperature	-65	+150	$^{\circ}$
VPWR	Consta Valle co	-0.3	6.0	V
IOVDD	Supply Voltage	-0.3	3.6	V
GPIO	Input voltage of GPIO (except PA7)	-0.3	3.6	V
HVTIO	Input voltage of HVT-IO (PA7)	-0.3	6.0	V

Note

3.2 ESD Ratings

Table 3-2 ESD Ratings

Parameter	Тур	Test pin	Reference standard
Human Body Mode	±8kV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±400V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±2kV	All pins	ANSI/ESDA/JEDEC JS-002-2022

3.3 PMU Characteristics

Table 3-3-1 PMU Characteristics under VPWR supply

	Table of Little Charles and Ch							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
VPWR	Power supply	-	2.7		5.5	V		
Operating mo	Operating mode							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
IOVDD	Voltage output			3.0		V		
טטעטו	Loading current	IOVDD=3.0V@VPWR = 3.7V			60	mA		
Low Power me	ode							
Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
IOVDD	Loading current	IOVDD=3.0V@VPWR = 3.7V			8	mA		

Table 3-3-2 PMU Characteristics under IOVDD supply

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
IOVDD	Power supply	-	1.8		3.6	V

^{1.}Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device.



3.4 IO Characteristics

Table 3-4 IO Characteristics

Input Chai	racteristics					
Symbol	Parameter	Conditions	10	Min	Max	Unit
V _{IL}	Low-Level Input Voltage	IOVDD = 3.0V	PAO~PA11	-0.3	1.4	V
			PA0~PA6			
	High-Level Input Voltage		PA8~PA11			
V_{IH}		IOVDD = 3.0V	USBDP	1.7	3.3	V
			USBDM			
		IOVDD = 3.0V	PA7	1.7	5.5	V
Output Ch	aracteristics					
Symbol	Parameter	Conditions	10	Ty	/p	Unit
				3(H	D=0)	
		IOVDD = 3.0V	PA0~PA6	9(H	D=1)	
		Voutput = 0.3V	PA8~PA11	21(H	D=2)	mA
I _{OL}	Output Current		76/	54(HD=3)		
			PA7			
		IOVDD = 3.0V	USBDP		3	mA
		Voutput = 0.3V	USBDM			
				3(HD=0) 9(HD=1) 21(HD=2) 54(HD=3)		
		IOVDD = 3.0V	PA0~PA6			mA
		Voutput = 2.7V	PA8~PA11			
I _{OH}	Output Current					
		10,100 3,01	PA7			
		IOVDD = 3.0V	USBDP		3	mA
		Voutput = 2.7V	USBDM			
Internal R	esistance Characteristics					
Symbol	Parameter	Conditions	10	Ty	ур	Unit
				10k(F	PU=1)	
		IOVDD = 3.0V	PAO~PA11	100k(PU=2)	Ω
R_{pu}	Pull-up Resistance			1M(PU=3)		
		IOVDD = 3.0V	USBDP	1.	5k	Ω
		IOVDD = 3.0V	USBDM	18	0k	Ω
				10k(I	PD=1)	
		IOVDD = 3.0V	PA0~PA11	100k(PD=2)	Ω
R_{pd}	Pull-down Resistance			1M(PD=3)		
		IOVDD = 3.0V	USBDP	15k		Ω
		$1 \times 10 \times 100 = 3 \times 100$	İ			

Note

1.Internal pull-up/pull-down resistance accuracy ±20%.



3.5 BT Characteristics

3.5.1 Transmitter

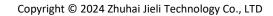
Table 3-5-1 Transmitter characteristics

Parameter	Conditions	Min	Тур	Max	Unit
Maximum RF Transmit Power	BLE-1Mbps		8	9	dBm

3.5.2 Receiver

Table 3-5-2 Receiver characteristics

Parameter	Conditions	Min	Тур	Max	Unit
	BLE-1Mbps		-96		dBm
	BLE-2Mbps	/	-93		dBm
Sensitivity	BLE-S2	\	-99		dBm
	BLE-S8	-	-103.5	//	dBm





4 Package Information

4.1 QFN20L_3×3mm

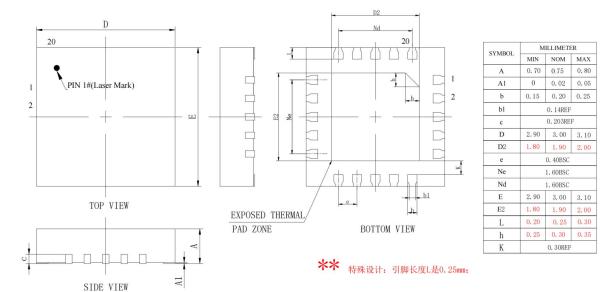


Figure 4-1 AW313A Package



5 IC Marking Information

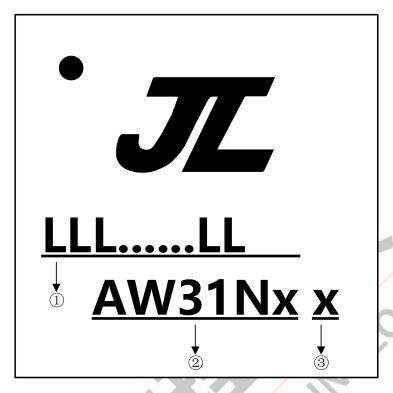


Figure 5-1 AW313A Package Outline

- 1 LLL.....LL LOT No., It contains 7 to 18 alphanumerics
- 2 AW31Nx Chip Model
- 3 x Built-in flash size
 - 0 No Flash Memory
 - 2 2Mbit Flash
 - 4 4Mbit Flash



6 Solder-Reflow Condition

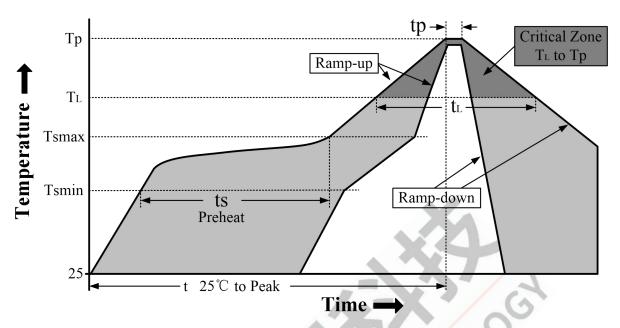


Figure 6-1 Classification Reflow Profile

Table 6-1 Classification Profiles

Profile Feature		Sn-Pb Eutectic Assembly	Pb-Free Assembly
	Temperature Min (T _{smin})	100°C	150℃
Preheat/Soak	Temperature Max (T _{smax})	150℃	200℃
	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds
Average ramp-up rate (T _{smax} to T _p)		3°C/second max	3°C/second max
Liquidus temperature (T _L)		183℃	217℃
Time (t _L) maintained above T _L		60-150 seconds	60-150 seconds
Peak package body temperature (T _p)		See Table 6-2	See Table 6-3
Time within 5℃ of actual		10-30 seconds	20-40 seconds
Peak Temperature (tp) ²		10-50 Seconds	
Ramp-down rate (Tp to TL)		6°C/second max	6°C/second max
Time 25°C to peak temperature		6 minutes max	8 minutes max

Note

- 1.All temperatures refer to topside of the package, measured on the package body surface
- 2.Time within 5℃ of actual peak temperature (tp) specified for the reflow profiles is a "supplier" and "user" maximum.

Table 6-2 SnPb Classification Temperature

Package	Volume mm ³	Volume mm³ ≥ 350	
Thickness	< 350		
<2.5 mm	240 +0/-5℃	225 +0/-5℃	
≥2.5 mm	225 +0/-5℃	225 +0/-5℃	



Table 6-3 Pb-free - Classification Temperature

	·				
Package	Volume mm³	Volume mm³	Volume mm³		
Thickness	< 350	350 - 2000	> 2000		
< 1.6mm	260℃	260℃	260℃		
1.6 mm - 2.5mm	260℃	250℃	245℃		
> 2.5mm	250℃	245℃	245℃		

Note

1.*Tolerance The device manufacturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0 $^{\circ}$ C.For example 260 $^{\circ}$ C+0 $^{\circ}$ C)at the rated MSL level.

